

## 6-Channel, 210-W, Digital-Amplifier Power Stage

### FEATURES

- **Total Output Power @ 10% THD+N**
  - 5×30 W @ 6 Ω + 1×60 W @ 3 Ω
- **105-dB SNR (A-Weighted)**
- **0.07% THD+N @ 1 W**
- **Power Stage Efficiency > 90% Into Recommended Loads (SE)**
- **Integrated Self-Protection Circuits**
  - Undervoltage
  - Overtemperature
  - Overload
  - Short Circuit
- **Integrated Active-Bias Control to Avoid DC Pop**
- **Thermally Enhanced 44-Pin HTSSOP Package**
- **EMI-Compliant When Used With Recommended System Design**

### APPLICATIONS

- DVD Receiver
- Home Theater in a Box

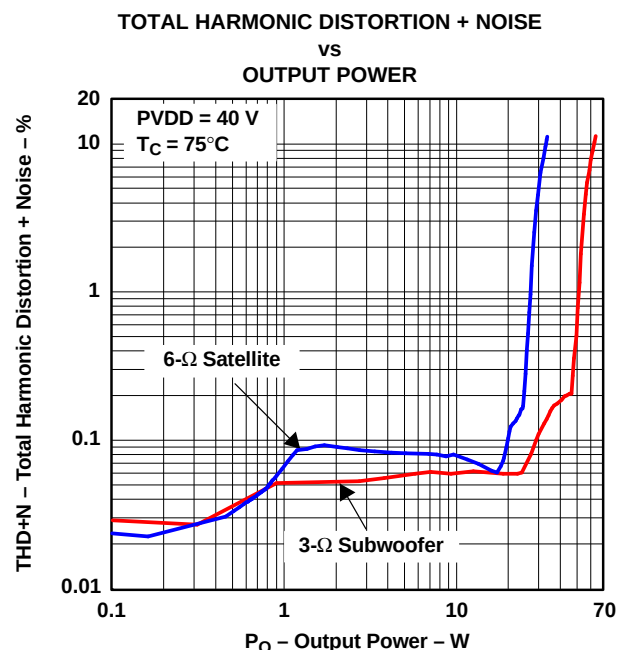
### DESCRIPTION

The TAS5186A is a high-performance, six-channel, digital-amplifier power stage with an improved protection system. The TAS5186A is capable of driving a 6-Ω, single-ended load up to 30 W per each front/satellite channel and a 3-Ω, single-ended subwoofer greater than 60 W at 10% THD+N performance.

A low-cost, high-fidelity audio system can be built using a TI chipset comprising a modulator (e.g., TAS5086) and the TAS5186A. This device does not require power-up sequencing because of the internal power-on reset.

The TAS5186A requires only simple passive demodulation filters on its outputs to deliver high-quality, high-efficiency audio amplification. The device efficiency of the TAS5186A is greater than 90% when driving 6-Ω satellites and a 3-Ω subwoofer speaker.

The TAS5186A has an innovative protection system integrated on-chip, safeguarding the device against a wide range of fault conditions that could damage the system. These safeguards are short-circuit protection, overload protection, undervoltage protection, and overtemperature protection. The TAS5186A has a new proprietary current-limiting circuit that reduces the possibility of device shutdown during high-level music transients. A new programmable overcurrent detector allows the use of lower-cost inductors in the demodulation output filter.



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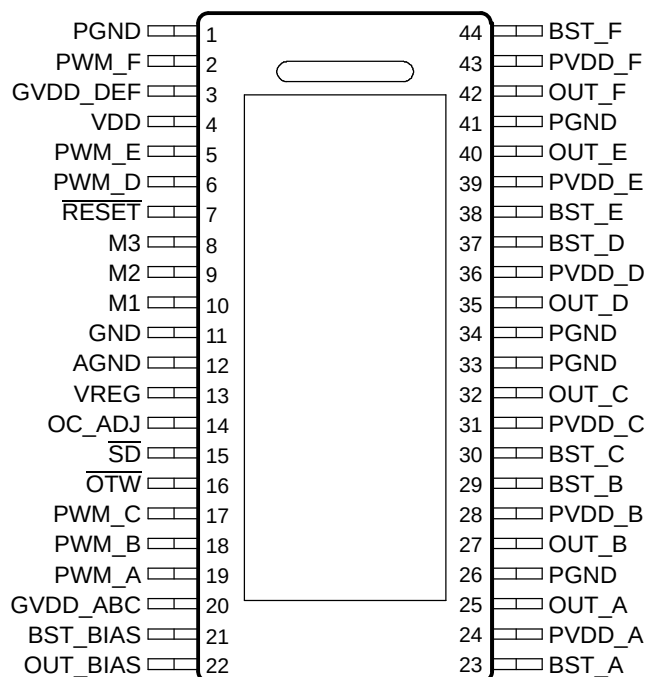
These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## GENERAL INFORMATION

### TERMINAL ASSIGNMENT

The TAS5186A is available in a thermally enhanced 44-pin HTSSOP PowerPAD™ package. The heat slug is located on the top side of the device for convenient thermal coupling to a heatsink.

**DDV PACKAGE  
(TOP VIEW)**



P0016-03

## GENERAL INFORMATION (continued)

### TERMINAL FUNCTIONS

| TERMINAL |                               | TYPE <sup>(1)</sup> | DESCRIPTION                                                        |
|----------|-------------------------------|---------------------|--------------------------------------------------------------------|
| NAME     | NO.                           |                     |                                                                    |
| AGND     | 12                            | P                   | Analog ground                                                      |
| BST_A    | 23                            | P                   | HS bootstrap supply (BST), capacitor to OUT_A required             |
| BST_B    | 29                            | P                   | HS bootstrap supply (BST), external capacitor to OUT_B required    |
| BST_BIAS | 21                            | P                   | BIAS bootstrap supply, external capacitor to OUT_BIAS required     |
| BST_C    | 30                            | P                   | HS bootstrap supply (BST), external capacitor to OUT_C required    |
| BST_D    | 37                            | P                   | HS bootstrap supply (BST), external capacitor to OUT_D required    |
| BST_E    | 38                            | P                   | HS bootstrap supply (BST), external capacitor to OUT_E required    |
| BST_F    | 44                            | P                   | HS bootstrap supply (BST), external capacitor to OUT_F required    |
| GND      | 11                            | P                   | Chip ground                                                        |
| GVDD_ABC | 20                            | P                   | Gate drive voltage supply                                          |
| GVDD_DEF | 3                             | P                   | Gate drive voltage supply                                          |
| M1       | 10                            | I                   | Mode selection pin                                                 |
| M2       | 9                             | I                   | Mode selection pin                                                 |
| M3       | 8                             | I                   | Mode selection pin                                                 |
| OC_ADJ   | 14                            | O                   | Overcurrent threshold programming pin, resistor to ground required |
| OTW      | 16                            | O                   | Overtemperature warning open-drain output signal, active-low       |
| OUT_A    | 25                            | O                   | Output, half-bridge A, satellite                                   |
| OUT_B    | 27                            | O                   | Output, half-bridge B, satellite                                   |
| OUT_BIAS | 22                            | O                   | BIAS half-bridge output pin                                        |
| OUT_C    | 32                            | O                   | Output, half-bridge C, subwoofer                                   |
| OUT_D    | 35                            | O                   | Output, half-bridge D, satellite                                   |
| OUT_E    | 40                            | O                   | Output, half-bridge E, satellite                                   |
| OUT_F    | 42                            | O                   | Output, half-bridge F, satellite                                   |
| PGND     | 1,<br>26,<br>33,<br>34,<br>41 | P                   | Power ground                                                       |
| PVDD_A   | 24                            | P                   | Power-supply input for half-bridge A                               |
| PVDD_B   | 28                            | P                   | Power-supply input for half-bridge B                               |
| PVDD_C   | 31                            | P                   | Power-supply input for half-bridge C                               |
| PVDD_D   | 36                            | P                   | Power-supply input for half-bridge D                               |
| PVDD_E   | 39                            | P                   | Power-supply input for half-bridge E                               |
| PVDD_F   | 43                            | P                   | Power-supply input for half-bridge F                               |
| PWM_A    | 19                            | I                   | PWM input signal for half-bridge A                                 |
| PWM_B    | 18                            | I                   | PWM input signal for half-bridge B                                 |
| PWM_C    | 17                            | I                   | PWM input signal for half-bridge C                                 |
| PWM_D    | 6                             | I                   | PWM input signal for half-bridge D                                 |
| PWM_E    | 5                             | I                   | PWM input signal for half-bridge E                                 |
| PWM_F    | 2                             | I                   | PWM input signal for half-bridge F                                 |
| RESET    | 7                             | I                   | Reset signal (active-low logic)                                    |
| SD       | 15                            | O                   | Shutdown open-drain output signal, active-low                      |
| VDD      | 4                             | P                   | Power supply for digital voltage regulator                         |
| VREG     | 13                            | O                   | Digital regulator supply filter pin, output                        |

(1) I = input; O = output; P = power

**Table 1. MODE Selection Pins**

| MODE PINS <sup>(1)</sup> |     | MODE     |                                                             |
|--------------------------|-----|----------|-------------------------------------------------------------|
| M2                       | M3  | NAME     | DESCRIPTION                                                 |
| 0                        | 0   | 2.1 mode | Channels A, B, and C enabled; channels D, E, and F disabled |
| 0                        | 1   | 5.1 mode | All channels enabled                                        |
| 1                        | 0/1 | Reserved |                                                             |

(1) M1 must always be connected to GND. 0 indicates a pin connected to GND; 1 indicates a pin connected to VREG.

**PACKAGE HEAT DISSIPATION RATINGS<sup>(1)</sup>**

| PARAMETER                                           | TAS5186ADDV          |
|-----------------------------------------------------|----------------------|
| $R_{\theta JC}$ (°C/W)—1 satellite (sat.) FET only  | 10.3                 |
| $R_{\theta JC}$ (°C/W)—1 subwoofer (sub.) FET only  | 5.2                  |
| $R_{\theta JC}$ (°C/W)—1 sat. half-bridge           | 5.2                  |
| $R_{\theta JC}$ (°C/W)—1 sub. half-bridge           | 2.6                  |
| $R_{\theta JC}$ (°C/W)—5 sat. half-bridges + 1 sub. | 1.74                 |
| Typical pad area <sup>(2)</sup>                     | 34.9 mm <sup>2</sup> |

(1) JC is junction-to-case, CH is case-to-heatsink.

(2)  $R_{\theta CH}$  is an important consideration. Assume a 2-mil thickness of typical thermal grease between the pad area and the heatsink. The  $R_{\theta CH}$  with this condition is typically 2°C/W for this package.

**ABSOLUTE MAXIMUM RATINGS**

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

| TAS5186A                                                       |                  |
|----------------------------------------------------------------|------------------|
| VDD to AGND                                                    | –0.3 V to 13.2 V |
| GVDD_X to AGND                                                 | –0.3 V to 13.2 V |
| PVDD_X to PGND_X <sup>(2)</sup>                                | –0.3 V to 50 V   |
| OUT_X to PGND_X <sup>(2)</sup>                                 | –0.3 V to 50 V   |
| BST_X to PGND_X <sup>(2)</sup>                                 | –0.3 V to 63.2 V |
| VREG to AGND                                                   | –0.3 V to 4.2 V  |
| PGND to GND                                                    | –0.3 V to 0.3 V  |
| PGND to AGND                                                   | –0.3 V to 0.3 V  |
| GND to AGND                                                    | –0.3 V to 0.3 V  |
| PWM_X, OC_ADJ, M1, M2, M3 to AGND                              | –0.3 V to 4.2 V  |
| RESET, SD, OTW to AGND                                         | –0.3 V to 7 V    |
| Maximum operating junction temperature range ( $T_J$ )         | 0 to 125°C       |
| Storage temperature                                            | –40°C to 125°C   |
| Lead temperature – 1.6 mm (1/16 inch) from case for 10 seconds | 260°C            |
| Minimum PWM pulse duration, low                                | 30 ns            |

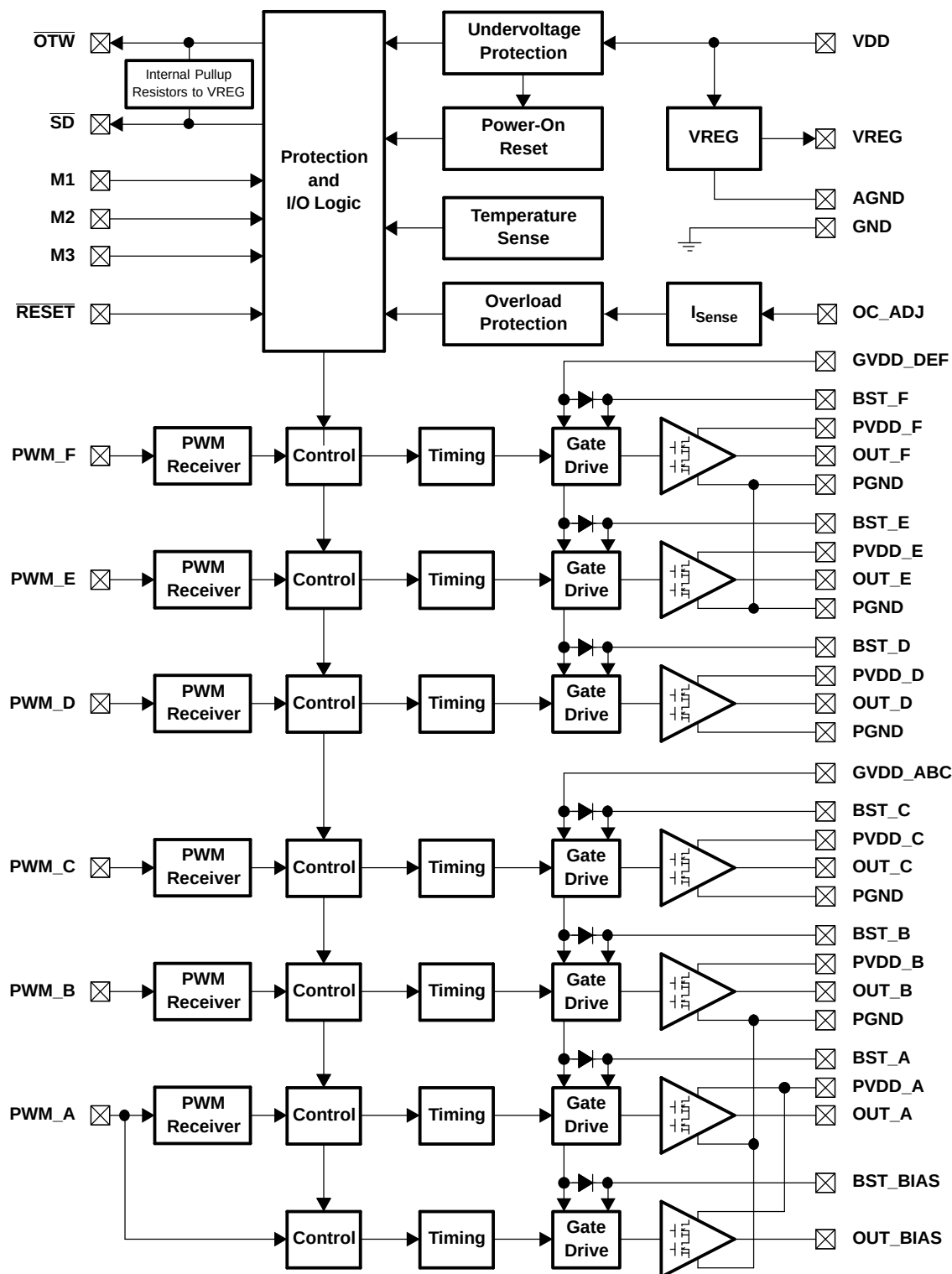
(1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) These voltages represent the dc voltage + peak ac waveform measured at the terminal of the device in all conditions.

## TYPICAL SYSTEM DIAGRAM

A schematic diagram for a typical system is appended at the end of the data sheet.

## FUNCTIONAL BLOCK DIAGRAM



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**RECOMMENDED OPERATING CONDITIONS**

|                  |                                                             |                                                         | MIN  | TYP | MAX  | UNIT     |
|------------------|-------------------------------------------------------------|---------------------------------------------------------|------|-----|------|----------|
| PVDD_X           | Half-bridge supply, SE                                      | DC supply voltage at pin(s)                             | 0    |     | 40   | V        |
| GVDD             | Gate drive and guard ring supply voltage                    | DC voltage at pin(s)                                    | 10.8 | 12  | 13.2 | V        |
| VDD              | Digital regulator supply                                    | DC supply voltage at pin                                | 10.8 | 12  | 13.2 | V        |
| VPU              | Pullup voltage supply                                       | Any value of $R_{PU,EXT}$ within recommended range      | 3    | 5   | 5.5  | V        |
| $R_{L,SAT}$      | Resistive load impedance, satellite channels <sup>(1)</sup> | Recommended demodulation filter                         | 4    | 6   |      | $\Omega$ |
| $R_{L,SUB}$      | Resistive load impedance, subwoofer channel                 | Recommended demodulation filter                         | 2.25 | 3   |      | $\Omega$ |
| $L_{output}$     | Demodulation filter inductance                              | Minimum output inductance under short-circuit condition | 5    | 22  |      | $\mu H$  |
| $C_{output,sat}$ | Demodulation filter capacitance                             |                                                         |      | 1   |      | $\mu F$  |
| $C_{output,sub}$ | Demodulation filter capacitance                             |                                                         |      | 1   |      | $\mu F$  |
| $F_{PWM}$        | PWM frame rate                                              |                                                         | 192  | 384 | 432  | kHz      |

(1) Load impedance outside range listed might cause shutdown due to OLP, OTE, or NLP.

**AUDIO SPECIFICATION**

PVDD\_X = 40 V, GVDD = 12 V, audio frequency = 1 kHz, AES17 measurement filter,  $F_{PWM} = 384$  kHz, case temperature = 75°C. Audio performance is recorded as a chipset, using TAS5086 PWM processor with an effective modulation index limit of 97%. All performance is in accordance with the foregoing specifications and recommended operating conditions unless otherwise specified.

| PARAMETER   |                                               | CONDITIONS                                                                                                                   | MIN | TYP   | MAX | UNIT    |
|-------------|-----------------------------------------------|------------------------------------------------------------------------------------------------------------------------------|-----|-------|-----|---------|
| $P_{O,sat}$ | Power output per satellite channel            | $R_L = 6 \Omega$ , 10% THD, clipped input signal                                                                             |     | 30    |     | W       |
|             |                                               | $R_L = 8 \Omega$ , 10% THD, clipped input signal                                                                             |     | 25    |     |         |
|             |                                               | $R_L = 6 \Omega$ , 0 dBFS, unclipped input signal                                                                            |     | 25    |     |         |
|             |                                               | $R_L = 8 \Omega$ , 0 dBFS, unclipped input signal                                                                            |     | 20    |     |         |
| $P_{O,sub}$ | Power output, subwoofer                       | $R_L = 3 \Omega$ , 10% THD, clipped input signal                                                                             |     | 60    |     | W       |
|             |                                               | $R_L = 4 \Omega$ , 10% THD, clipped input signal                                                                             |     | 52    |     |         |
|             |                                               | $R_L = 3 \Omega$ , 0 dBFS, unclipped input signal                                                                            |     | 50    |     |         |
|             |                                               | $R_L = 4 \Omega$ , 0 dBFS, unclipped input signal                                                                            |     | 40    |     |         |
| THD + N     | Total harmonic distortion + noise, satellite  | $R_L = 6 \Omega$ , $P_O = 25$ W                                                                                              |     | 0.3%  |     |         |
|             |                                               | $R_L = 6 \Omega$ , 1 W                                                                                                       |     | 0.07% |     |         |
|             | Total harmonic distortion + noise, subwoofer  | $R_L = 3 \Omega$ , $P_O = 50$ W                                                                                              |     | 0.5%  |     |         |
|             |                                               | $R_L = 3 \Omega$ , 1 W                                                                                                       |     | 0.05% |     |         |
| $V_n$       | Output integrated noise, satellite            | A-weighted                                                                                                                   |     | 55    |     | $\mu V$ |
|             | Output integrated noise, subwoofer            | A-weighted                                                                                                                   |     | 60    |     |         |
| SNR         | System signal-to-noise ratio                  | A-weighted                                                                                                                   |     | 105   |     | dB      |
| DNR         | Dynamic range <sup>(1)</sup>                  | A-weighted, –60 dBFS input signal, measured with TAS5086 PWM processor                                                       |     | 105   |     | dB      |
| $P_{idle}$  | Power dissipation due to idle losses (IPVDDX) | $P_O = 0$ W, all channels running 5.1 mode <sup>(2)</sup> . 22- $\mu H$ Kwang-Sung inductors (see schematic for information) |     | 4.5   |     | W       |
|             |                                               | $P_O = 0$ W, 2.1 mode. 22- $\mu H$ Kwang-Sung inductors (see schematic for information)                                      |     | 2.2   |     | W       |

(1) SNR is calculated relative to 0-dBFS input level.

(2) Actual system idle losses are affected by core losses of output inductors.

## ELECTRICAL CHARACTERISTICS

$F_{PWM} = 384 \text{ kHz}$ ,  $GVDD = 12 \text{ V}$ ,  $VDD = 12 \text{ V}$ ,  $T_C$  (case temperature) =  $75^\circ\text{C}$ , unless otherwise noted. All performance is in accordance with recommended operating conditions, unless otherwise specified.

| SYMBOL                                             | PARAMETER                                                                          | CONDITIONS                                                                          | MIN  | TYP | MAX | UNIT    |
|----------------------------------------------------|------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|------|-----|-----|---------|
| INTERNAL VOLTAGE REGULATOR AND CURRENT CONSUMPTION |                                                                                    |                                                                                     |      |     |     |         |
| VREG                                               | Voltage regulator, only used as reference node                                     | VDD = 12 V                                                                          | 3    | 3.3 | 3.6 | V       |
| IVDD                                               | VDD supply current                                                                 | Operating, 50% duty cycle                                                           |      | 7   | 20  | mA      |
|                                                    |                                                                                    | Idle, reset mode                                                                    |      | 6   | 16  |         |
| IGVDD_X                                            | Gate supply current per half-bridge                                                | 50% duty cycle                                                                      |      | 5   | 22  | mA      |
|                                                    |                                                                                    | Idle, reset mode                                                                    |      | 1   | 3   |         |
| IPVDD_X                                            | Half-bridge idle current                                                           | 50% duty cycle, without output filter or load, 5.1 mode. 22-μH Kwang-Sung inductors |      | 110 |     | mA      |
|                                                    |                                                                                    | 50% duty cycle, without output filter or load, 2.1 mode. 22-μH Kwang-Sung inductors |      | 60  |     |         |
| OUTPUT STAGE MOSFETS                               |                                                                                    |                                                                                     |      |     |     |         |
| R <sub>DSon</sub> , LS Sat                         | Drain-to-source resistance, low side, satellite                                    | T <sub>J</sub> = 25°C, includes metallization resistance                            |      | 210 |     | mΩ      |
| R <sub>DSon</sub> , HS Sat                         | Drain-to-source resistance, high side, satellite                                   | T <sub>J</sub> = 25°C, includes metallization resistance                            |      | 210 |     | mΩ      |
| R <sub>DSon</sub> , LS Sub                         | Drain-to-source resistance, low side, subwoofer                                    | T <sub>J</sub> = 25°C, includes metallization resistance                            |      | 110 |     | mΩ      |
| R <sub>DSon</sub> , HS Sub                         | Drain-to-source resistance, high side, subwoofer                                   | T <sub>J</sub> = 25°C, includes metallization resistance                            |      | 110 |     | mΩ      |
| I/O PROTECTION                                     |                                                                                    |                                                                                     |      |     |     |         |
| V <sub>UVP</sub> , G                               | Undervoltage protection limit GVDD_X                                               |                                                                                     |      | 10  |     | V       |
| V <sub>UVP</sub> , hyst <sup>(1)</sup>             | Undervoltage protection hysteresis                                                 |                                                                                     |      | 250 |     | mV      |
| OTW <sup>(1)</sup>                                 | Overtemperature warning                                                            |                                                                                     |      | 125 |     | °C      |
| OTW <sub>hyst</sub> <sup>(1)</sup>                 | Temperature drop needed below OTW temp. for OTW to be inactive after the OTW event |                                                                                     |      | 25  |     | °C      |
| OTE <sup>(1)</sup>                                 | Overtemperature error                                                              |                                                                                     |      | 155 |     | °C      |
| OTE <sub>HYST</sub> <sup>(1)</sup>                 | Temperature drop needed below OTE temp. for SD to be released after the OTE event  |                                                                                     |      | 25  |     | °C      |
| OLCP                                               | Overload protection counter                                                        |                                                                                     | 1.25 |     |     | ms      |
| I <sub>OC</sub>                                    | Overcurrent limit protection, satellite                                            | R <sub>ocp</sub> = 18 kΩ                                                            |      | 4.5 |     | A       |
|                                                    | Overcurrent limit protection, subwoofer                                            | R <sub>ocp</sub> = 18 kΩ                                                            |      | 8   |     | A       |
| I <sub>OCT</sub>                                   | Overcurrent response time                                                          |                                                                                     |      | 210 |     | ns      |
| R <sub>ocp</sub>                                   | OC programming resistor range                                                      | Resistor tolerance = 5%                                                             |      | 18  |     | kΩ      |
| STATIC DIGITAL SPECIFICATION                       |                                                                                    |                                                                                     |      |     |     |         |
| V <sub>IH</sub>                                    | High-level input voltage                                                           | PWM_X, M1, M2, M3, RESET                                                            | 2    |     |     | V       |
| V <sub>IL</sub>                                    | Low-level input voltage                                                            |                                                                                     |      | 0.8 |     |         |
| I <sub>LEAK</sub>                                  | Input leakage current                                                              | Static condition                                                                    | -80  |     | 80  | μA      |
| OTW/SHUTDOWN (SD)                                  |                                                                                    |                                                                                     |      |     |     |         |
| R <sub>INT_PU</sub>                                | Internal pullup resistor to DREG (3.3 V) for SD and OTW                            |                                                                                     |      | 26  |     | kΩ      |
| V <sub>OH</sub>                                    | High-level output voltage                                                          | Internal pullup resistor only                                                       | 3    | 3.3 | 3.6 | V       |
|                                                    |                                                                                    | External pullup: 4.7-kΩ resistor to 5 V                                             | 4.5  |     | 5   |         |
| V <sub>OL</sub>                                    | Low-level output voltage                                                           | I <sub>O</sub> = 4 mA                                                               |      | 0.2 | 0.4 |         |
| FANOUT                                             | Device fanout OTW, SD                                                              | No external pullup                                                                  |      | 30  |     | Devices |

(1) Specified by design.

## TYPICAL CHARACTERISTICS, 5.1 MODE

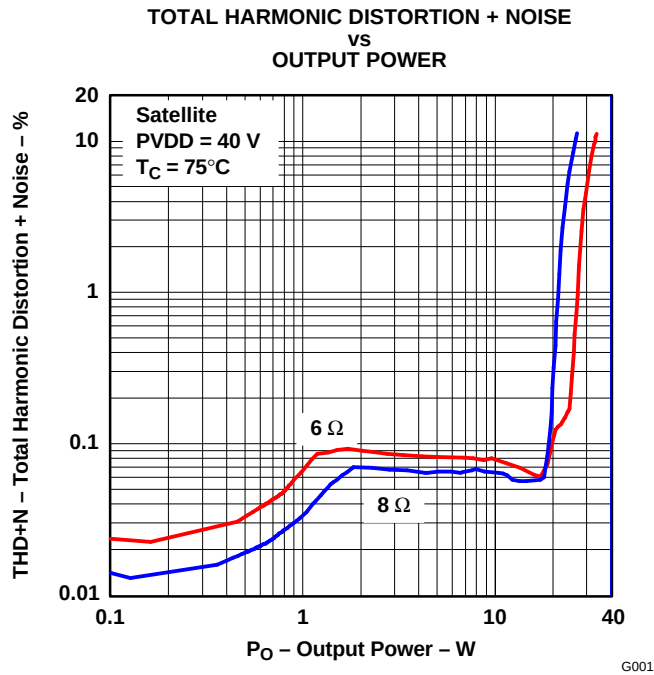


Figure 1.

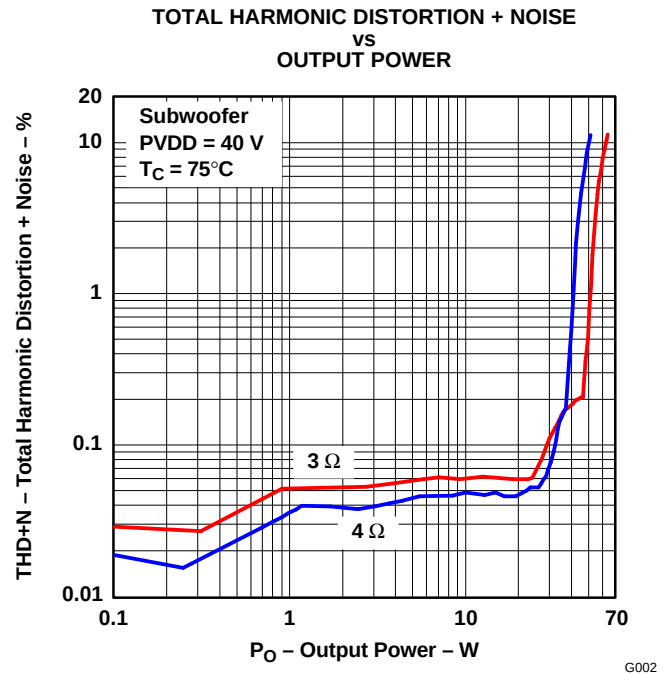


Figure 2.

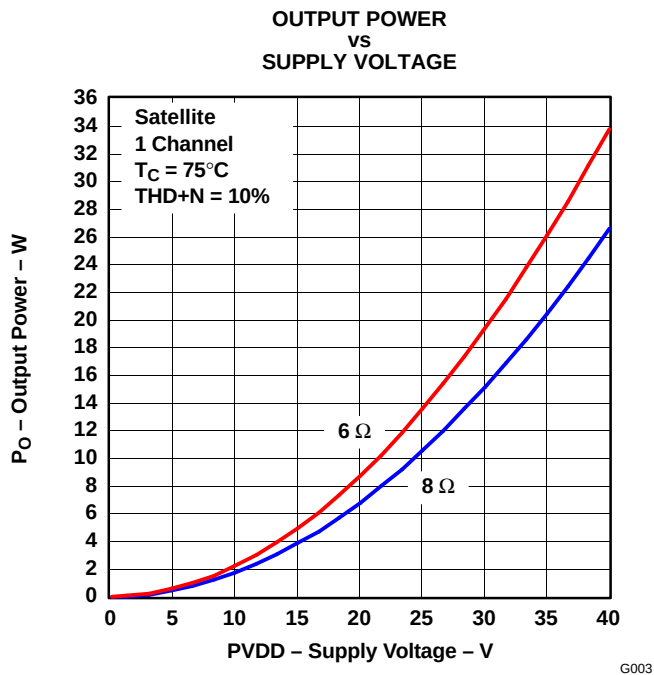


Figure 3.

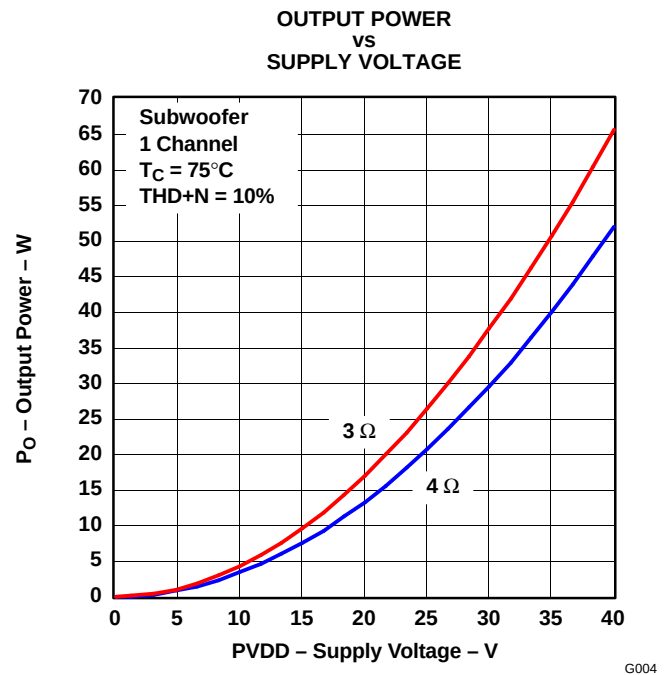


Figure 4.



# TYPICAL CHARACTERISTICS, 5.1 MODE (continued)

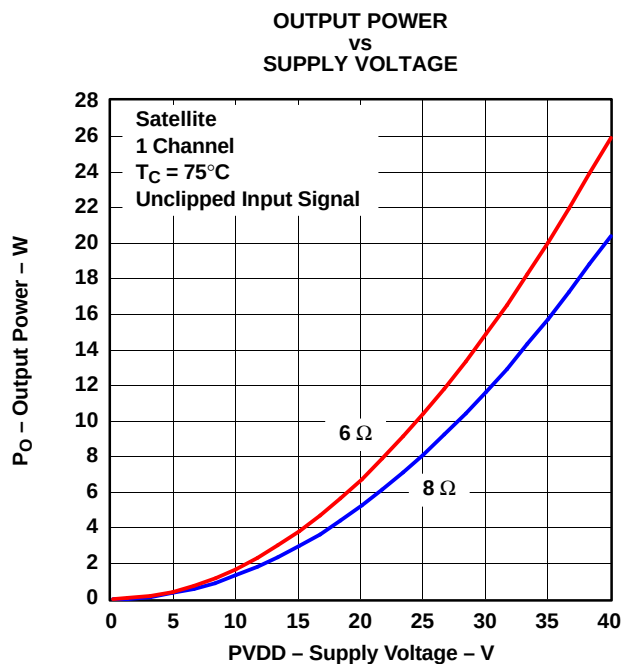


Figure 5.

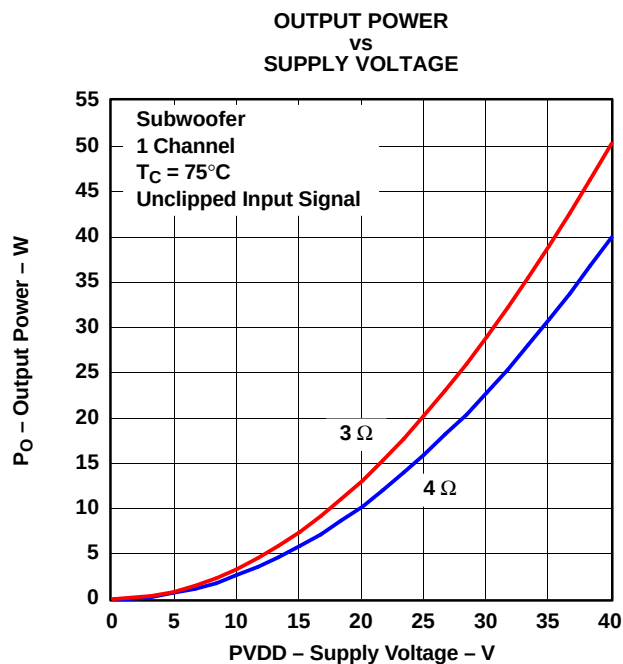


Figure 6.

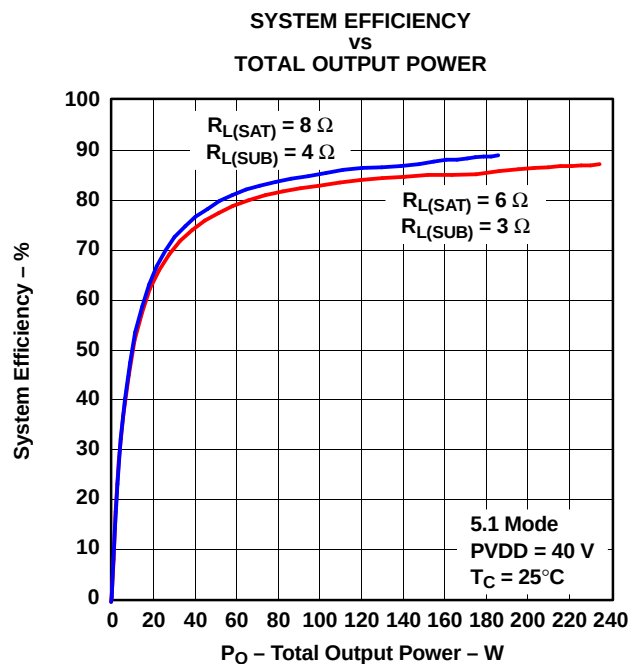


Figure 7.

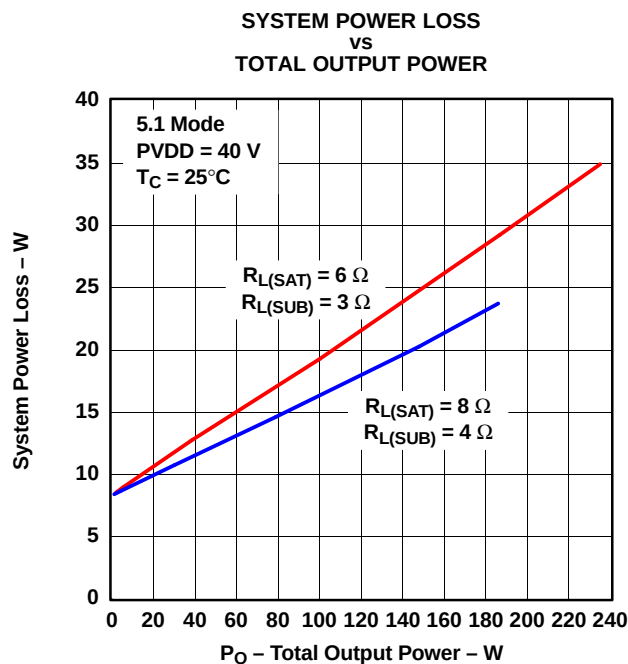
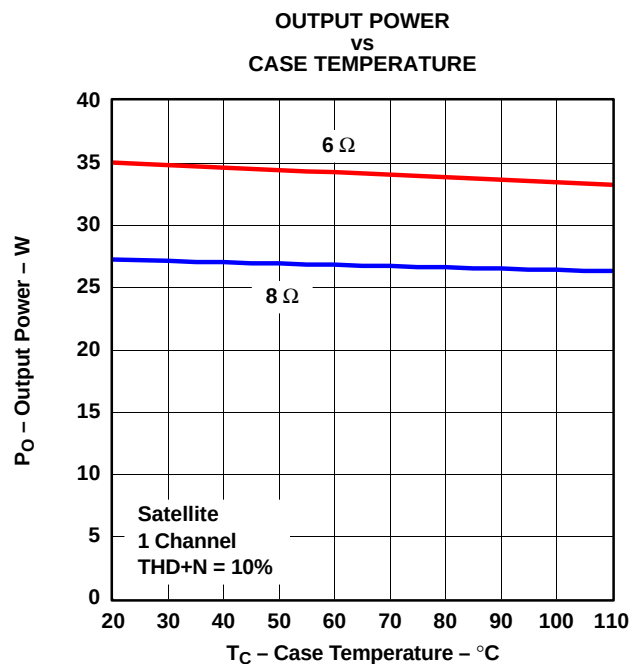


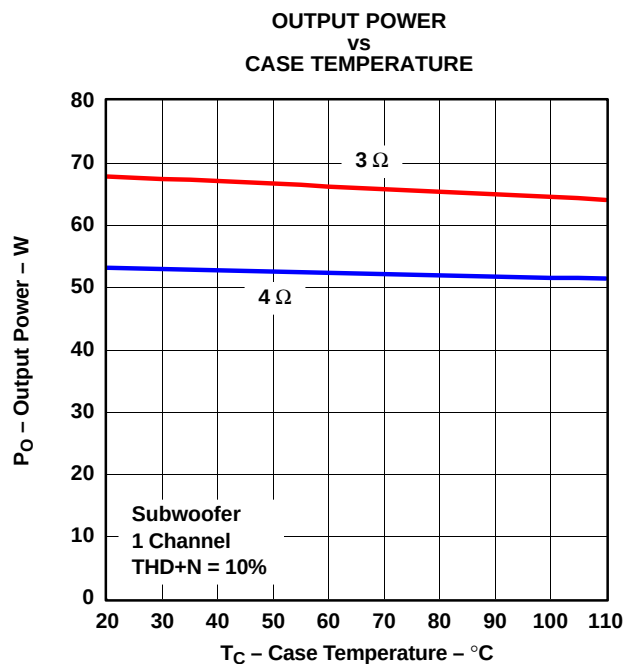
Figure 8.

## TYPICAL CHARACTERISTICS, 5.1 MODE (continued)



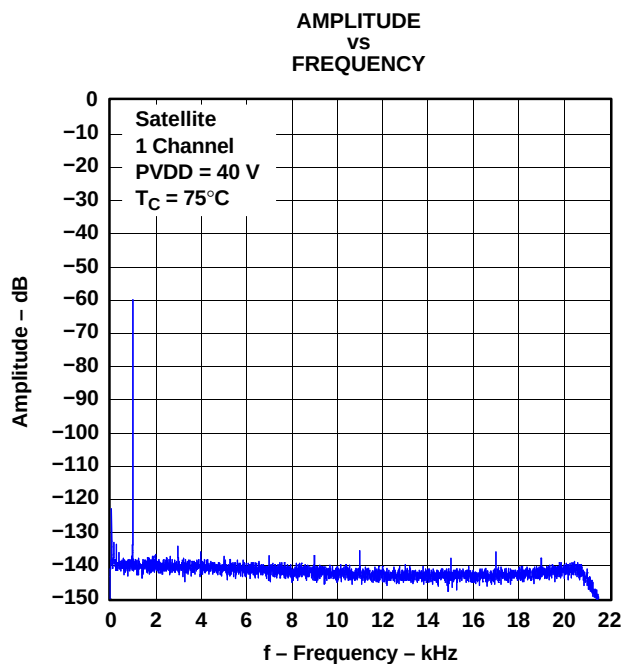
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Figure 9.



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Figure 10.



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Figure 11.

## THEORY OF OPERATION

### POWER SUPPLIES

To facilitate system design, the TAS5186A needs only a 12-V supply in addition to a typical 39-V power-stage supply. An internal voltage regulator provides suitable voltage levels for the digital and low-voltage analog circuitry. Additionally, all circuitry requiring a floating voltage supply, e.g., the high-side gate drive, is accommodated by built-in bootstrap circuitry requiring only a few external capacitors.

In order to provide outstanding electrical and acoustic characteristics, the PWM signal path including gate drive and output stage is designed as identical, independent half-bridges. For this reason, each half-bridge has separate bootstrap pins (BST\_X) and power-stage supply pins (PVDD\_X). Furthermore, an additional pin (VDD) is provided as power supply for all common circuits. Although supplied from the same 12-V source, it is highly recommended to separate GVDD\_X and VDD on the printed-circuit board (PCB) by RC filters (see application diagram for details). These RC filters provide the recommended high-frequency isolation. Special attention should be paid to placing all decoupling capacitors as close to their associated pins as possible. In general, inductance between the power-supply pins and decoupling capacitors must be avoided. (See reference board documentation for additional information.)

For a properly functioning bootstrap circuit, a small ceramic capacitor must be connected from each bootstrap pin (BST\_X) to the power-stage output pin (OUT\_X). When the power-stage output is low, the bootstrap capacitor is charged through an internal diode connected between the gate-drive power-supply pin (GVDD\_X) and the bootstrap pin. When the power-stage output voltage is high, the bootstrap capacitor voltage is shifted above the output voltage potential and thus provides a suitable voltage supply for the high-side gate driver. In an application with PWM switching frequencies in the range 352 kHz to 384 kHz, it is recommended to use 33-nF ceramic capacitors, size 0603 or 0805, for the bootstrap capacitor. These 33-nF capacitors ensure sufficient energy storage, even during minimal PWM duty cycles, to keep the high-side power stage FET (LDMOS) fully started during all of the remaining part of the PWM cycle. In an application running at a reduced switching frequency, generally 250 kHz to 192 kHz, the bootstrap capacitor might need to be increased in value. Special attention should be paid to the power-stage power supply; this includes component selection, PCB placement and routing. As indicated, each half-bridge has independent power-stage supply pins (PVDD\_X). For optimal electrical performance, EMI compliance, and system

reliability, it is important that each PVDD\_X pin is decoupled with a 100-nF ceramic capacitor placed as close as possible to each supply pin on the same side of the PCB as the TAS5186A. It is recommended to follow the PCB layout of the TAS5186A reference design. For additional information on the recommended power supply and required components, see the application diagrams given in this data sheet. The 12-V supply should be powered from a low-noise, low-output-impedance voltage regulator. Likewise, the 39-V power-stage supply is assumed to have low output impedance and low noise. The power-supply sequence is not critical due to the internal power-on-reset circuit. Moreover, the TAS5186A is fully protected against erroneous power-stage turnon due to parasitic gate charging. Thus, voltage-supply ramp rates (dv/dt) are typically noncritical.

### SYSTEM POWER-UP/DOWN SEQUENCE

The TAS5186A does not require a power-up sequence. The outputs of the H-bridge remain in a high-impedance state until the gate-drive supply voltage (GVDD\_X) and VDD voltage are above the undervoltage protection (UVP) voltage threshold (see the *Electrical Characteristics* section of this data sheet). Although not specifically required, it is recommended to hold  $\overline{\text{RESET}}$  in a low state while powering up the device.

When the TAS5186A is being used with TI PWM modulators such as the TAS5086, no special attention to the state of  $\overline{\text{RESET}}$  is required, provided that the chipset is configured as recommended.

### Powering Down

The TAS5186A does not require a power-down sequence. The device remains fully operational as long as the gate-drive supply (GVDD\_X) voltage and VDD voltage are above the undervoltage protection (UVP) threshold level (see the *Electrical Characteristics* section of this data sheet). Although not specifically required, it is a good practice to hold  $\overline{\text{RESET}}$  low during power down, thus preventing audible artifacts including pops and clicks.

When the TAS5186A is being used with TI PWM modulators such as the TAS5086, no special attention to the state of  $\overline{\text{RESET}}$  is required, provided that the chipset is configured as recommended.

### Error Reporting

The  $\overline{\text{SD}}$  and  $\overline{\text{OTW}}$  pins are both active-low, open-drain outputs. Their function is for protection-mode signaling to a PWM controller or other system-control device.

Any fault resulting in device shutdown is signaled by the  $\overline{SD}$  pin going low. Likewise,  $\overline{OTW}$  goes low when the device junction temperature exceeds 125°C (see the following table).

| $\overline{SD}$ | $\overline{OTW}$ | DESCRIPTION                                                              |
|-----------------|------------------|--------------------------------------------------------------------------|
| 0               | 0                | Overtemperature (OTE) or overload (OLP) or undervoltage (UVP)            |
| 0               | 1                | Overload (OLP) or undervoltage (UVP)                                     |
| 1               | 0                | Overtemperature warning. Junction temperature higher than 125°C, typical |
| 1               | 1                | Normal operation. Junction temperature lower than 125°C, typical         |

It should be noted that asserting  $\overline{RESET}$  low forces the  $\overline{SD}$  and  $\overline{OTW}$  signals high independently of faults being present. It is recommended to monitor the  $\overline{OTW}$  signal using the system microcontroller and to respond to an overtemperature warning signal by, e.g., turning down the volume to prevent further heating of the device that would result in device shutdown (OTE). To reduce external component count, an internal pullup resistor to 3.3 V is provided on both the  $\overline{SD}$  and  $\overline{OTW}$  outputs. Level compliance for 5-V logic can be obtained by adding external pullup resistors to 5 V (see the *Electrical Characteristics* section of this data sheet for further specifications).

### Device Protection System

The TAS5186A contains advanced protection circuitry carefully designed to facilitate system integration and ease of use, as well as safeguarding the device from permanent failure due to a wide range of fault conditions such as short circuit, overload, and undervoltage. The TAS5186A responds to a fault by immediately setting the power stage in a high-impedance state (Hi-Z) and asserting the  $\overline{SD}$  pin low. In situations other than overload, the device automatically recovers when the fault condition has been removed, e.g., the supply voltage has increased or the temperature has dropped. For highest possible reliability, recovering from an overload fault requires external reset of the device no sooner than 1 second after the shutdown (see the *Device Reset* section of this data sheet).

### OVERCURRENT (OC) PROTECTION WITH CURRENT LIMITING AND OVERLOAD DETECTION

The device has independent, fast-reacting current detectors with programmable trip threshold (OC threshold) on all high-side and low-side power-stage FETs. See the following table for OC-adjust resistor values. The detector outputs are closely monitored by

two protection systems. The first protection system controls the power stage in order to prevent the output current from further increasing. i.e., it performs a current-limiting function rather than prematurely shutting down during combinations of high-level music transients and extreme speaker load-impedance drops. If the high-current situation persists, i.e., the power stage is being overloaded, a second protection system triggers a latching shutdown, resulting in the power stage being set in the high-impedance (Hi-Z) state.

For added flexibility, the OC threshold is programmable within a limited range using a single external resistor connected between the OC\_ADJ pin and AGND.

| OC-Adjust Resistor Values (k $\Omega$ ) | Maximum Peak Current Before OC Occurs (A) |
|-----------------------------------------|-------------------------------------------|
| 18                                      | 4.5 (sat.), 8 (sub.)                      |

It should be noted that a properly functioning overcurrent detector assumes the presence of a properly designed demodulation filter at the power-stage output. Short-circuit protection is not provided directly at the output pins of the power stage but only on the speaker terminals (after the demodulation filter). It is required to follow certain guidelines when selecting the OC threshold and an appropriate demodulation inductor.

- For the lowest-cost bill of materials in terms of component selection, the OC threshold current should be limited, considering the power output requirement and minimum load impedance. Higher-impedance loads require a lower OC threshold.
- The demodulation filter inductor must retain at least 5  $\mu$ H of inductance at twice the OC threshold setting.

Most inductors have decreasing inductance with increasing temperature and increasing current (saturation). To some degree, an increase in temperature naturally occurs when operating at high output currents, due to inductor core losses and the dc resistance of the inductor copper winding. A thorough analysis of inductor saturation and thermal properties is strongly recommended.

Setting the OC threshold too low might cause issues such as lack of output power and/or unexpected shutdowns due to sensitive overload detection.

In general, it is recommended to follow closely the external component selection and PCB layout as given in the application section.

## Overtemperature Protection

The TAS5186A has a two-level temperature-protection system that asserts an active-low warning signal ( $\overline{\text{OTW}}$ ) when the device junction temperature exceeds 125°C (typical), and if the device junction temperature exceeds 155°C (typical), the device is put into thermal shutdown, resulting in all half-bridge outputs being set in the high-impedance state (Hi-Z) and  $\overline{\text{SD}}$  being asserted low.

## UNDERVOLTAGE PROTECTION (UVP) AND POWER-ON RESET (POR)

The UVP and POR circuits of the TAS5186A fully protect the device in any power-up/down and brownout situation. While powering up, the POR circuit resets the overload circuit (OLP) and ensures that all circuits are fully operational when the GVDD\_X and VDD supply voltages reach 10 V (typical). Although GVDD\_X and VDD are independently monitored, a supply voltage drop below the UVP threshold on any VDD or GVDD\_X pin results in all half-bridge outputs immediately being set in the high-impedance (Hi-Z) state and  $\overline{\text{SD}}$  being asserted low. The device automatically resumes operation when all supply voltages have increased above the UVP threshold.

## DEVICE RESET

When  $\overline{\text{RESET}}$  is asserted low, the output FETs in all half-bridges are forced into a high-impedance (Hi-Z) state.

Asserting the  $\overline{\text{RESET}}$  input low removes any fault information to be signaled on the  $\overline{\text{SD}}$  output, i.e.,  $\overline{\text{SD}}$  is forced high.

A rising-edge transition on the  $\overline{\text{RESET}}$  input allows the device to resume operation after an overload fault.

## ACTIVE-BIAS CONTROL (ABC)

Audible pop noises are often associated with single-rail, single-ended power stages at power-up or at the start of switching. This commonly known problem has been virtually eliminated by incorporating a proprietary active-bias control circuitry as part of the TAS5186A feature set. By the use of only a few passive external components (typically resistors), the ABC can pre-charge the dc-blocking

element in the audio path, i.e., split-cap capacitors or series capacitor, to the desired potential before switching is started on the PWM outputs. (For recommended configuration, see the typical application schematic included in this data sheet).

The start-up sequence can be controlled through sequencing the M3 and  $\overline{\text{RESET}}$  pins according to Table 2 and Table 3.

**Table 2. 5.1 Mode—All Output Channels Active**

| M3 | $\overline{\text{RESET}}$ | OUT_BIAS | OUT_A,<br>_B, _C | OUT_D,<br>_E, _F | COMMENT                                        |
|----|---------------------------|----------|------------------|------------------|------------------------------------------------|
| 0  | 0                         | Hi-Z     | Hi-Z             | Hi-Z             | All outputs disabled, nothing is switching.    |
| 1  | 0                         | Active   | Hi-Z             | Hi-Z             | OUT_BIAS enabled, all other outputs disabled   |
| 1  | 1                         | Hi-Z     | Active           | Active           | OUT_BIAS disabled, all other outputs switching |

**Table 3. 2.1 Mode—Only Output Channels A, B, and C Active**

| M3 | $\overline{\text{RESET}}$ | OUT_BIAS | OUT_A,<br>_B, _C | OUT_D,<br>_E, _F | COMMENT                                        |
|----|---------------------------|----------|------------------|------------------|------------------------------------------------|
| 0  | 0                         | Hi-Z     | Hi-Z             | Hi-Z             | All outputs disabled, nothing is switching.    |
| 1  | 0                         | Active   | Hi-Z             | Hi-Z             | OUT_BIAS enabled, all other outputs disabled   |
| 0  | 1                         | Hi-Z     | Active           | Hi-Z             | OUT_BIAS disabled, all other outputs switching |

When the TAS5186A is used with the TAS5086 PWM modulator, no special attention to start-up sequencing is required, provided that the chipset is configured as recommended.



## PACKAGING INFORMATION

| Orderable part number        | Status<br>(1) | Material type<br>(2) | Package   Pins    | Package qty   Carrier | RoHS<br>(3) | Lead finish/<br>Ball material<br>(4) | MSL rating/<br>Peak reflow<br>(5) | Op temp (°C) | Part marking<br>(6) |
|------------------------------|---------------|----------------------|-------------------|-----------------------|-------------|--------------------------------------|-----------------------------------|--------------|---------------------|
| <a href="#">TAS5186ADDV</a>  | Active        | Production           | HTSSOP (DDV)   44 | 35   TUBE             | Yes         | NIPDAU                               | Level-3-260C-168 HR               | 0 to 70      | 5186A               |
| TAS5186ADDV.A                | Active        | Production           | HTSSOP (DDV)   44 | 35   TUBE             | Yes         | NIPDAU                               | Level-3-260C-168 HR               | 0 to 70      | 5186A               |
| <a href="#">TAS5186ADDVR</a> | Active        | Production           | HTSSOP (DDV)   44 | 2000   LARGE T&R      | Yes         | NIPDAU                               | Level-3-260C-168 HR               | 0 to 70      | 5186A               |
| TAS5186ADDVR.A               | Active        | Production           | HTSSOP (DDV)   44 | 2000   LARGE T&R      | Yes         | NIPDAU                               | Level-3-260C-168 HR               | 0 to 70      | 5186A               |

<sup>(1)</sup> **Status:** For more details on status, see our [product life cycle](#).

<sup>(2)</sup> **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

<sup>(4)</sup> **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

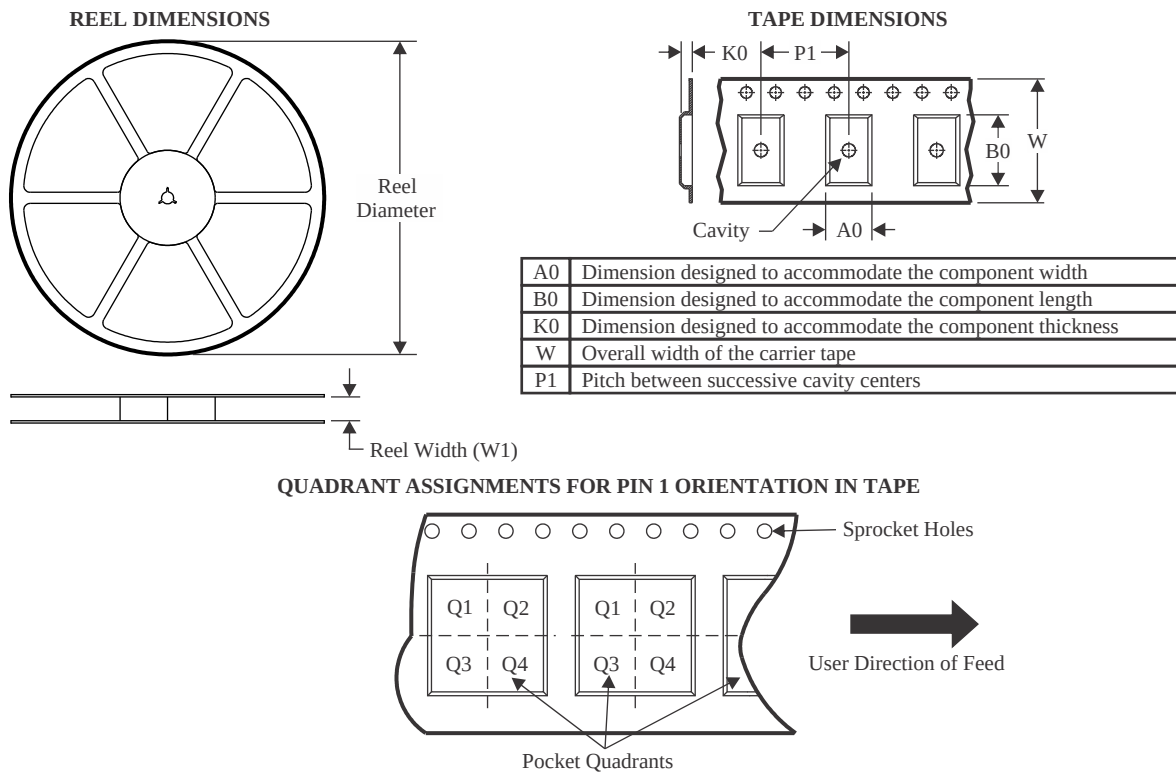
<sup>(6)</sup> **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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## TAPE AND REEL INFORMATION

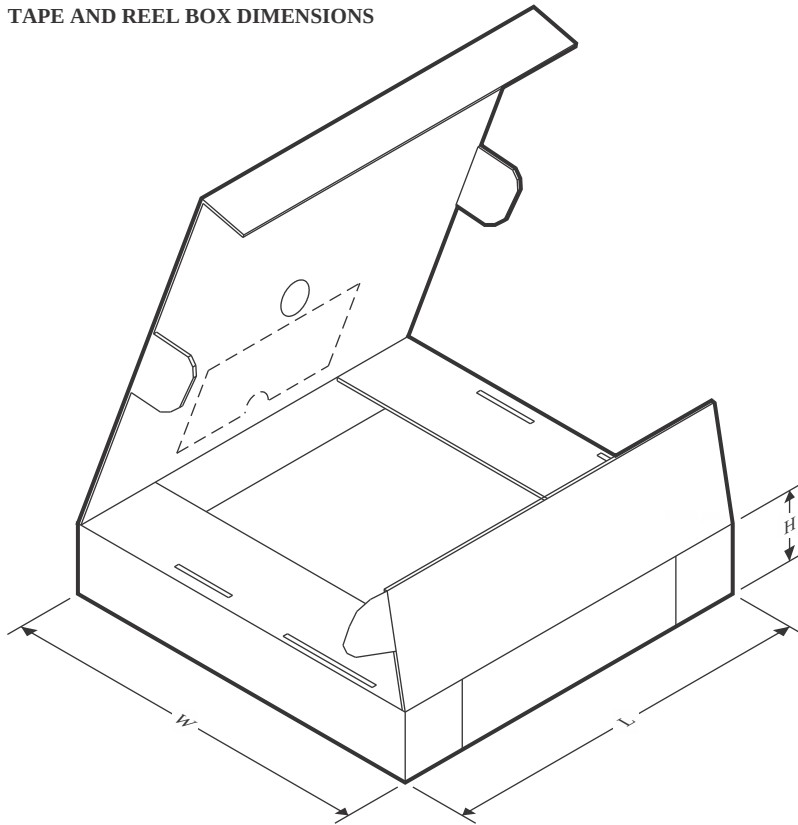


\*All dimensions are nominal

| Device       | Package Type | Package Drawing | Pins | SPQ  | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|--------------|--------------|-----------------|------|------|--------------------|--------------------|---------|---------|---------|---------|--------|---------------|
| TAS5186ADDVR | HTSSOP       | DDV             | 44   | 2000 | 330.0              | 24.4               | 8.6     | 15.6    | 1.8     | 12.0    | 24.0   | Q1            |



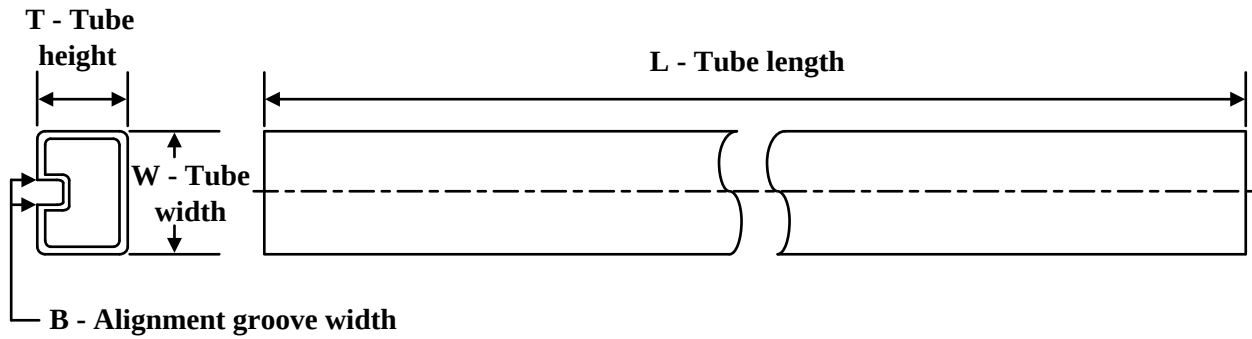
## TAPE AND REEL BOX DIMENSIONS



\*All dimensions are nominal

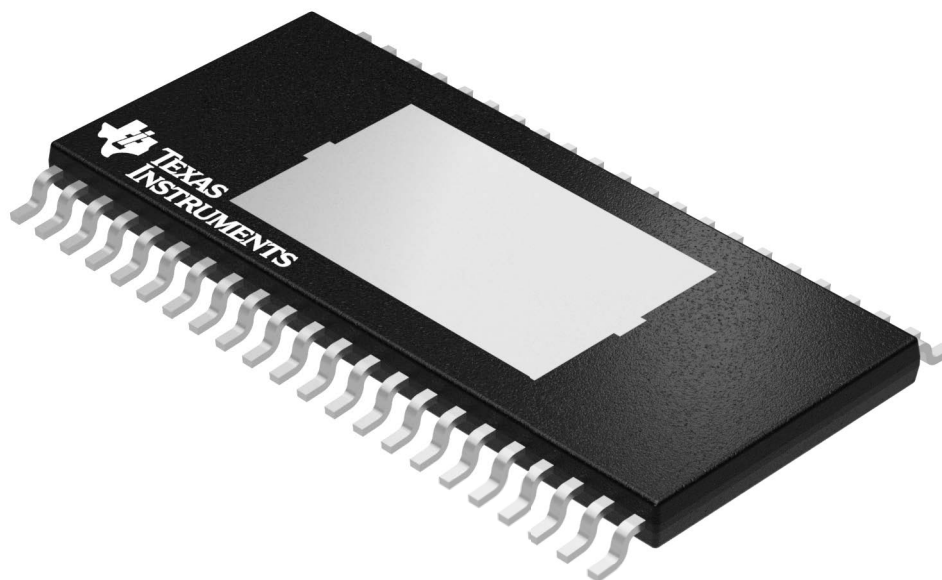
| Device       | Package Type | Package Drawing | Pins | SPQ  | Length (mm) | Width (mm) | Height (mm) |
|--------------|--------------|-----------------|------|------|-------------|------------|-------------|
| TAS5186ADDVR | HTSSOP       | DDV             | 44   | 2000 | 350.0       | 350.0      | 43.0        |

## TUBE



\*All dimensions are nominal

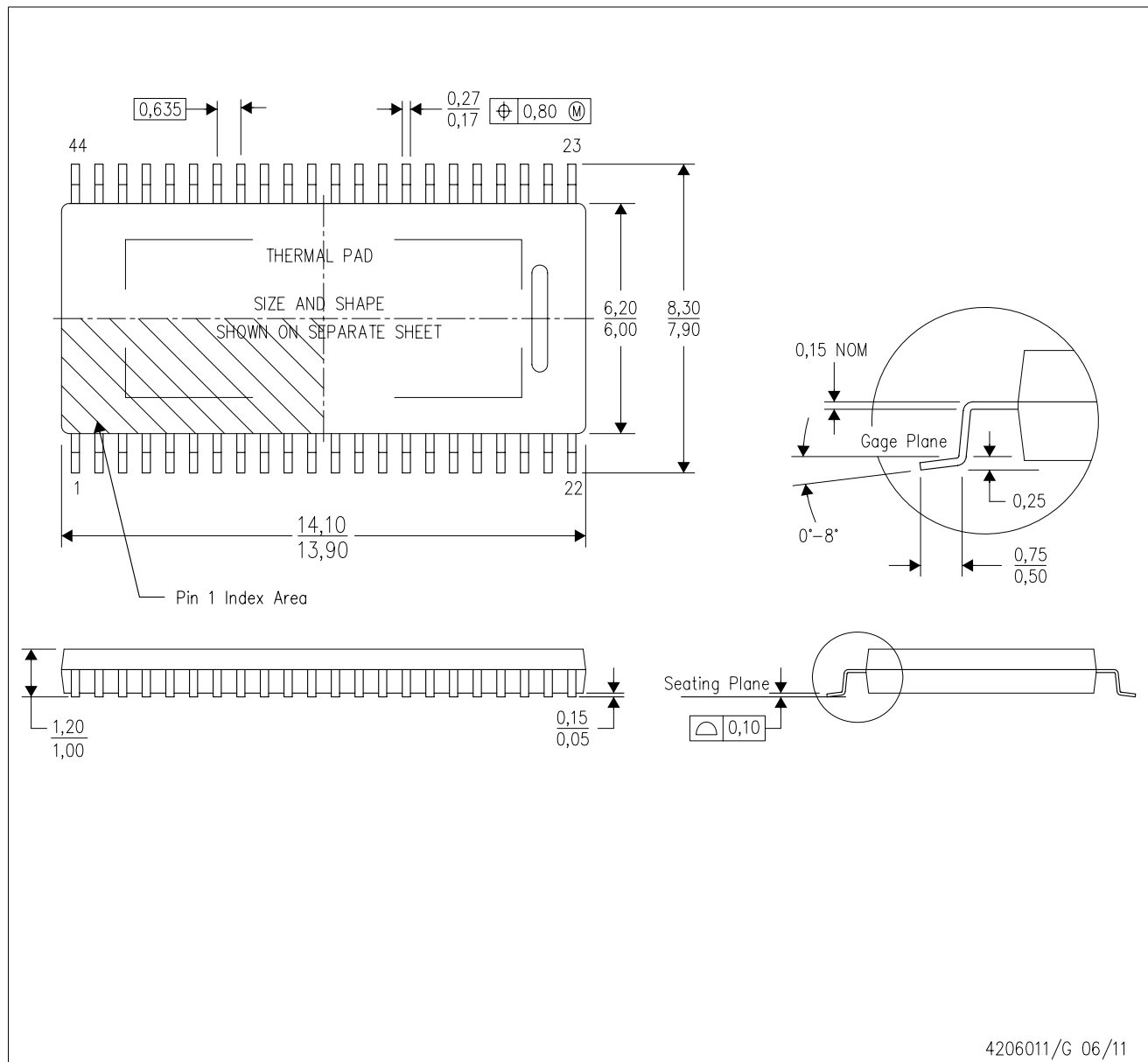
| Device        | Package Name | Package Type | Pins | SPQ | L (mm) | W (mm) | T (μm) | B (mm) |
|---------------|--------------|--------------|------|-----|--------|--------|--------|--------|
| TAS5186ADDV   | DDV          | HTSSOP       | 44   | 35  | 530    | 11.89  | 3600   | 4.9    |
| TAS5186ADDV.A | DDV          | HTSSOP       | 44   | 35  | 530    | 11.89  | 3600   | 4.9    |



Images above are just a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.

## MECHANICAL DATA

DDV (R-PDSO-G44) PowerPAD™ PLASTIC SMALL OUTLINE PACKAGE (DIE DOWN)



- NOTES:
- All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
  - This drawing is subject to change without notice.
  - Body dimensions do not include mold flash or protrusion not to exceed 0,15.
  - This package is designed to be attached directly to an external heatsink. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at [www.ti.com](http://www.ti.com) <<http://www.ti.com>>. See the product data sheet for details regarding the exposed thermal pad dimensions.

PowerPAD is a trademark of Texas Instruments.

DDV (R-PDSO-G44)

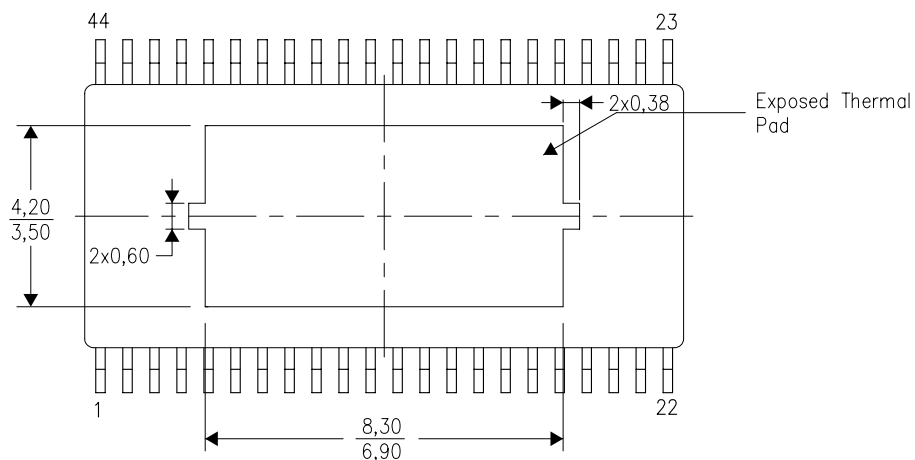
PowerPAD™ SMALL OUTLINE PACKAGE

## THERMAL INFORMATION

This PowerPAD™ package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at [www.ti.com](http://www.ti.com).

The exposed thermal pad dimensions for this package are shown in the following illustration.



Top View

Exposed Thermal Pad Dimensions

4206975-2/D 07/11

NOTE: All linear dimensions are in millimeters

PowerPAD is a trademark of Texas Instruments

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Last updated 10/2025